NSN 5961-00-189-1511

Thyristor Semiconductor Device - Page 1 of 2



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Inclosure Material:
Metal County Languist County C
Overall Length: 1.125 inches
Mounting Facility Quantity:
1 Internal Configuration:
Junction contact
Mounting Method:
Threaded stud
Features Provided:
Hermetically sealed case
Overall Width Across Flats:
Between 1.031 inches and 1.062 inches
Thread Size:
0.500 inches
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
10.0 off-state voltage, peak and 600.0 off-state voltage, rms total and 5.0 gate voltage, dc
Current Rating Per Characteristic:
2.00 amperes forward current, total rms of standard range and 50.00 amperes forward current, total rms megahertz
Power Rating Per Characteristic:
5.0 watts small-signal input power, common-collector blank
Maximum Operating Tempurature Per Measurement Point:
125.0 degrees celsius ambient air
Special Features:
Junction pattern arrangement: pnpn
Test Data Document:
81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Thread Series Designator:
Unf
Terminal Type And Quantity:
2 tab, solder lug and 1 threaded stud
Specification Data:
81349-mil-s-19500/204 government specification
Shelf Life:
N/a
Unit Of Measure:

No

Demilitarization:

NSN 5961-00-189-1511

Thyristor Semiconductor Device - Page 2 of 2



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